## 1N6263WS

## SILICON SCHOTTKY BARRIER DIODE

for general purpose applications

PINNING

| PIN | DESCRIPTION |
| :---: | :--- |
| 1 | Cathode |
| 2 | Anode |



Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Peak Reverse Voltage | $\mathrm{V}_{\text {RRM }}$ | 40 | V |
| Max. Single Cycle Surge Forward Current (10 s Square wave) | $\mathrm{I}_{\text {FSM }}$ | 2 | A |
| Power Dissipation | $\mathrm{P}_{\text {tot }}$ | $400^{1)}$ | mW |
| Junction Temperature | $\mathrm{T}_{\mathrm{j}}$ | 200 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\mathrm{S}}$ | -55 to +200 | ${ }^{\circ} \mathrm{C}$ |
| ${ }^{1)}$ Valid provided the leads direct at the case are kept at ambient temperature. |  |  |  |

Characteristics at $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Min. | Max. | Unit |
| :--- | :---: | :---: | :---: | :---: |
| Reverse Breakdown Voltage <br> at $\mathrm{I}_{\mathrm{R}}=10 \mu \mathrm{~A}$ | $\mathrm{~V}_{(\mathrm{BR}) \mathrm{R}}$ | 40 | - | V |
| Forward Voltage <br> at $\mathrm{I}_{\mathrm{F}}=1 \mathrm{~mA}$ <br> at $\mathrm{I}_{\mathrm{F}}=15 \mathrm{~mA}$ | $\mathrm{~V}_{\mathrm{F}}$ | - | 0.39 | V |
| Leakage Current <br> at $\mathrm{V}_{\mathrm{R}}=30 \mathrm{~V}$ | $\mathrm{I}_{\mathrm{R}}$ | - | 200 | nA |
| Junction Capacitance <br> at $\mathrm{V}_{\mathrm{R}}=0$ V, $\mathrm{f}=1 \mathrm{MHz}$ | $\mathrm{C}_{\mathrm{tot}}$ | - | 2.2 | pF |
| Reverse Recovery Time <br> at $\mathrm{I}_{\mathrm{F}}=\mathrm{I}_{\mathrm{R}}=5 \mathrm{~mA}$, Recover to $0.1 \mathrm{I}_{\mathrm{R}}$ | $\mathrm{t}_{\mathrm{rr}}$ | - | 1 | ns |



5 Typ.Total Capacitance vs Reverse Voltage


®

## PACKAGE OUTLINE



